L	Hits	Search Text	DB	Time stamp
Number				
1	7654	((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/787) or (438/948) or (438/949) or (438/948) or (438/949) or (438/948) or (438/949) or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24
2	859	(438/950)).CCLS. (((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/946) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:13
4	0	(((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/787) or (438/774) or (438/982) or (438/984) or (438/996) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and ((bilayer or (bi adj2 layer)) near5 resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:35
5	0	i '	USPAT;	2004/07/24
		or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/772) or (438/774) or (438/787) or (438/984) or (438/984) or (438/984) or (438/9850)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and ((bilayer or (bi adj2 layer)) near10 resist)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	19:36
6	1		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:36
3	319		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:51

. 1				
8	or (438/64 (438/671) (438/765) (438/772) (438/787) (438/948) (438/950)) (si or sil and transi drain)) an near10 (in	(637) or (438/639) or (438/640) (1) or (438/666) or (438/669) or or (438/672) or (438/762) or or (438/770) or (438/771) or or (438/774) or (438/782) or or (438/906) or (438/947) or or (438/949) or .CCLS.) and (photoresist near10 icon or sylyated or silated))) stor and gate and (source or id (selective\$2 near10 deposit\$3 isulat\$3 or dielectric))) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24
9	0 (((((438/6 or (438/64 (438/671) (438/765) (438/772) (438/787) (438/948) (438/950)) (si or sil and transi	lj phase adj oxide) (37) or (438/639) or (438/640) (1) or (438/666) or (438/669) or or (438/672) or (438/762) or or (438/770) or (438/771) or or (438/774) or (438/782) or or (438/906) or (438/947) or or (438/949) or .CCLS.) and (photoresist near10 .icon or sylyated or silated))) .stor and gate and (source or ad (liquid adj phase adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24
10	0 (((((438/6 or (438/64 (438/671) (438/765) (438/772) (438/787) (438/948) (438/950)) (si_or_sil	(11quid ad) phase ad) oxide; (37) or (438/639) or (438/640) or (438/666) or (438/669) or or (438/770) or (438/771) or or (438/774) or (438/782) or or (438/906) or (438/947) or or (438/949) or .CCLS.) and (photoresist near10 .icon—or—syl-yated—or—silated)).stor and gate and (source or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:53
7	drain)) an or lpod) (((((438/64 or (438/64) (438/671) (438/765) (438/772) (438/787) (438/948) (438/950)) (si or sil and transi drain)) an	d ((liquid adj phase adj oxide)  (37) or (438/639) or (438/640)  (1) or (438/666) or (438/669) or  or (438/672) or (438/762) or  or (438/770) or (438/771) or  or (438/774) or (438/782) or  or (438/906) or (438/947) or  or (438/949) or  .CCLS.) and (photoresist near10  .icon or sylyated or silated)))  .stor and gate and (source or  id (selective\$2 near10 deposit\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:13
11	242 (438/\$.ccl adj aligne	usulat\$3 or dielectric)) s. or 257/\$.ccls.) and ((self ed adj contact) or (borderless et)) and bitline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/24 20:08
12	adj aligne adj contac	els. or 257/\$.ccls.) and ((self ed adj contact) or (borderless et)) and bitline) and (liquid adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/24 20:57
13	adj aligne adj contac (selective	els. or 257/\$.ccls.) and ((self ed adj contact) or (borderless et)) and bitline) and es2 near10 deposit\$3 near10 et or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/24 20:04
14	255 (438/\$.ccl adj aligne	s. or 257/\$.ccls.) and ((self ed adj contact) or sac or es adj contact)) and bitline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/24 20:12

	, Ł				
1	15	13	((438/\$.ccls. or 257/\$.ccls.) and ((self	USPAT;	2004/07/24
-			adj aligned adj contact) or sac or	US-PGPUB;	20:09
- [			(borderless adj contact)) and bitline)	EPO; JPO;	
			not ((438/\$.ccls. or 257/\$.ccls.) and	DERWENT;	
			((self adj aligned adj contact) or	IBM TDB	
			(borderless adj contact)) and bitline)	_	
	16	2612	(438/\$.ccls. or 257/\$.ccls.) and ((self	USPAT;	2004/07/24
			adj aligned adj contact) or sac or	US-PGPUB;	20:57
			(borderless adj contact)) and (source or	EPO; JPO;	
			drain)	DERWENT;	
		}	·	IBM TDB	
	17	121	((438/\$.ccls. or 257/\$.ccls.) and ((self	USPAT;	2004/07/24
			adj aligned adj contact) or sac or	US-PGPUB;	20:57
			(borderless adj contact)) and (source or	EPO; JPO;	
			drain)) and (selective\$2 near10 deposit\$3	DERWENT;	.
			near10 (insulat\$3 or dielectric))	IBM TDB	
	18	2.4	(((438/\$.ccls. or 257/\$.ccls.) and ((self	USPAT;	2004/07/24
	10		adj aligned adj contact) or sac or	US-PGPUB;	20:24
			(borderless adj contact)) and (source or	EPO; JPO;	
			drain)) and (selective\$2 near10 deposit\$3	DERWENT;	
i			near10 (insulat\$3 or dielectric))) and	IBM TDB	
i			(photoresist near10 (si or silicon or	12122	]
l			sylvated or silated))		
į	19	14		USPAT;	2004/07/24
1	19	1 1	("5565376") or ("5583358") or ("5696036")	US-PGPUB;	20:56
			or ("5872041")).PN.	EPO; JPO;	20.30
			OI ( 3072041 /).FW:	DERWENT;	
1				IBM TDB	
	20	329	((438/256) or (438/399)).CCLS.	USPAT;	2004/07/24
	20	329	((438/238) OI (438/399)).CCID.	US-PGPUB;	20:56
		ŀ		EPO; JPO;	20.30
				DERWENT;	
				-IBM-TDB	
_	-22		((((438/256) or (438/399)).CCLS.) and	USPAT;	2004/07/24
	22	0	((self adj aligned adj contact) or sac or	US-PGPUB;	20:57
			(borderless adj contact)) and (source or	EPO; JPO;	20.37
		i	drain)) and (selective\$2 near10 deposit\$3	DERWENT;	
				IBM TDB	
	23	0	near10 (insulat\$3 or dielectric)) (((((438/256) or (438/399)).CCLS.) and	USPAT;	2004/07/24
	23	0		US-PGPUB;	20:57
			((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or	EPO; JPO;	20.37
			drain)) and (selective\$2 near10 deposit\$3	DERWENT;	1
				i .	1
			near10 (insulat\$3 or dielectric))) and (liquid adj phase adj oxide)	IBM_TDB	1
	2.4	_	((((438/256) or (438/399)).CCLS.) and	USPAT;	2004/07/24
	24	1		· ·	20:58
			((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or	US-PGPUB; EPO; JPO;	20.30
			drain)) and (liquid adj phase adj oxide)	DERWENT;	
	0.1	4-1	///A20/256\ am //20/200\\ agt c \ am 3	IBM_TDB	2004/07/24
	21	41	(((438/256) or (438/399)).CCLS.) and	USPAT;	
			((self adj aligned adj contact) or sac or	US-PGPUB;	20:58
			(borderless adj contact)) and (source or	EPO; JPO;	
			drain)	DERWENT;	
				IBM_TDB	